



WANSEMI
万芯半导体

WP4N65KD

Enhancement Mode N-Channel Power MOSFET

TO-252/NMOS/650V/±30V/3V/4A/2.3Ω

Rev0.9

650V,2.3Ω, 4A, N-Channel MOSFET

1.Features

- ◆ New technology for high voltage device
- ◆ Low on-resistance and low conduction losses
- ◆ Ultra Low Gate Charge cause lower driving requirements

V _{DS} Typ.	R _{DS(on)} Typ.	I _D Max.
650V	2.3Ω @ 10V	4A

2.Applications

- ◆ Power factor correction
- ◆ Switched mode power supplies
- ◆ Uninterruptible Power Supply



Pin Description
TO-252



Schematic Diagram

3.Package Marking and Ordering Information

Part no.	Marking	Package	PCS/Reel	PCS/CTN.
WP4N65KD	WP4N65	TO-252	2,500	25,000

4.Absolute Max Ratings at Ta=25°C (Note1)

Parameter	Symbol	Maximum	Units
Drain to Source Voltage	V _{DSS}	650	V
Gate to Source Voltage	V _{GSS}	±30	V
Drain Current-Continuous	I _D	4	A
Drain Current (Pulse)	I _{DM}	16	A
Single Pulsed Avalanche Energy	E _{AS}	155	mJ
Maximum Power Dissipation	P _D	28.4	W
Operating Junction and Storage Temperature Range	T _j , T _{stg}	-55 to +160	°C

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

5. Thermal Resistance Ratings (Note 2)

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	4.4	$^{\circ}\text{C/W}$

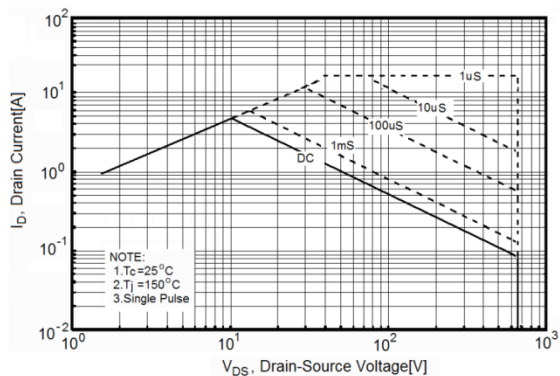
Note 2: When mounted on 1 inch square copper board $t \leq 10\text{sec}$ The value in any given application depends on the user's specific board design.

6. Electrical Characteristics at $T_a=25^{\circ}\text{C}$ (Note 3)

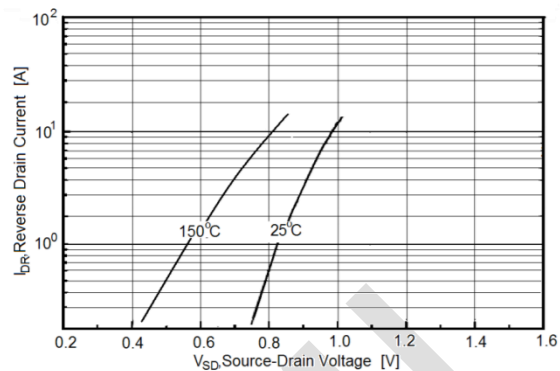
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	650			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 650\text{V}$, $V_{GS} = 0\text{V}$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{DS}=250\mu\text{A}$	2.4	3.0	4.0	V
Drain to Source On-State Resistance	$R_{DS(on)}$	$I_D = 2\text{A}$, $V_{GS} = 10\text{V}$		2.3	2.5	Ω
Input Capacitance	C_{iss}	$V_{GS}=0\text{V}$, $V_{DS}=50\text{V}$, Frequency=1.0MHz		304		pF
Output Capacitance	C_{oss}			18		pF
Reverse Transfer Capacitance	C_{rss}			0.6		pF
Turn-ON Delay Time	$t_{d(on)}$			8		ns
Turn-ON Rise Time	t_r	$V_{DD} = 380\text{V}$, $V_{GS} = 10\text{V}$, $R_{GEN} = 5\Omega$, $I_D = 2.5\text{A}$		4		ns
Turn-OFF Delay Time	$t_{d(off)}$			52		ns
Turn-ON Fall Time	t_f			9		ns
Total Gate Charge	Q_g	$V_{DS} = 480\text{V}$, $V_{GS} = 10\text{V}$, $I_D = 4\text{A}$		8.8		nC
Gate-Source Charge	Q_{gs}			2.3		nC
Gate-Drain Charge	Q_{gd}			4		nC
Diode Forward Voltage	V_{SD}	$I_S = 4\text{A}$, $V_{GS} = 0\text{V}$	0.55	0.8	1.1	V
Maximum Continuous Drain to Source Diode Forward Current	I_S	-	-	-	4	A
Maximum Pulsed Drain to Source Diode Forward Current	I_{SM}	-	-	-	16	A
Body Diode Reverse Recovery Time	t_{rr}	$I_F=2\text{A}$, $di/dt=100\text{A}/\mu\text{s}$	-	200	-	nS
Body Diode Reverse Recovery Charg	Q_{rr}		-	0.6	-	nC

Note 3: Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

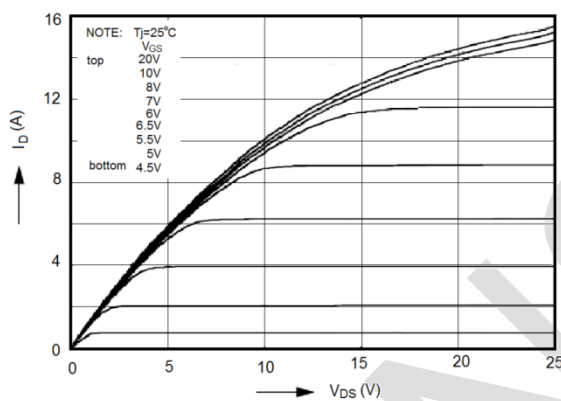
7. Typical electrical and thermal characteristics



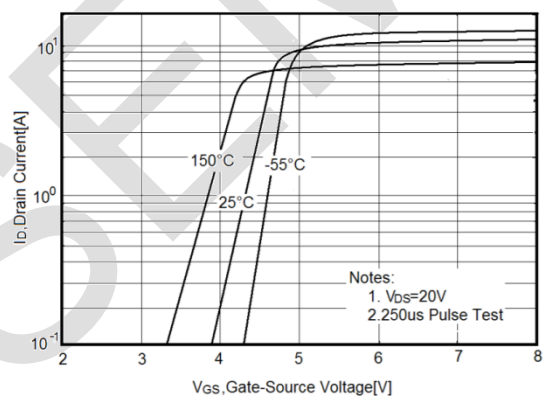
Safe operating area



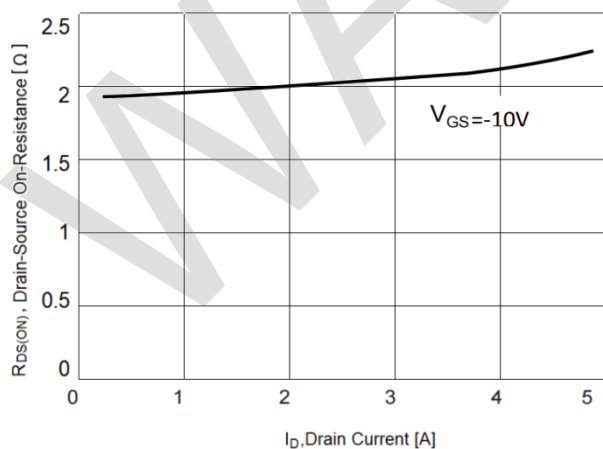
Source-Drain Diode Forward Voltage



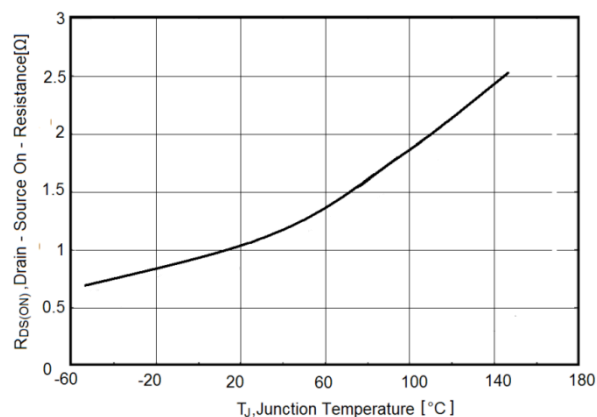
Output Characteristics



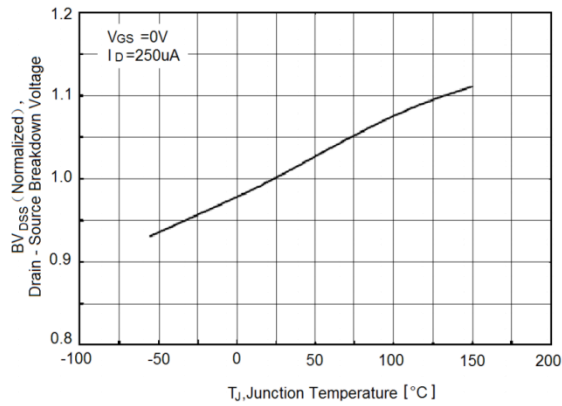
Typical Transfer Characteristics



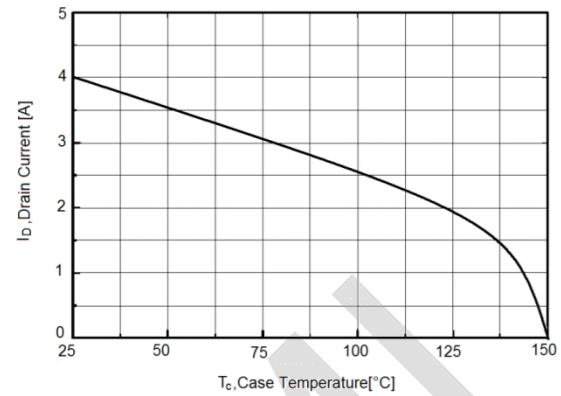
Static drain-source on resistance



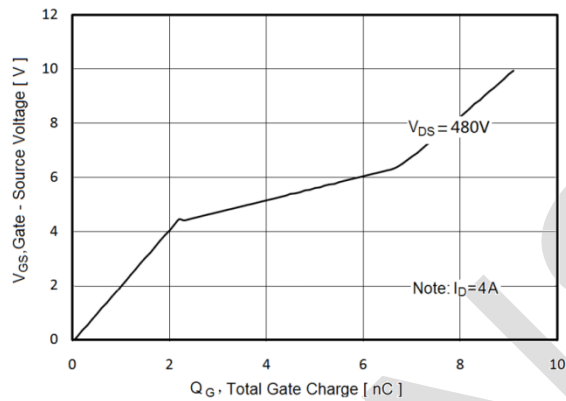
$R_{DS(on)}$ vs Junction Temperature



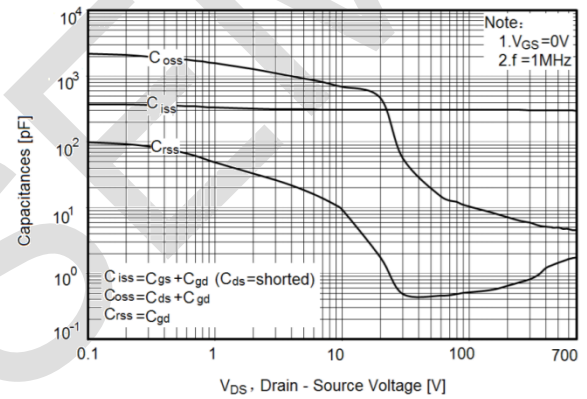
BV_{DSS} vs Junction Temperature



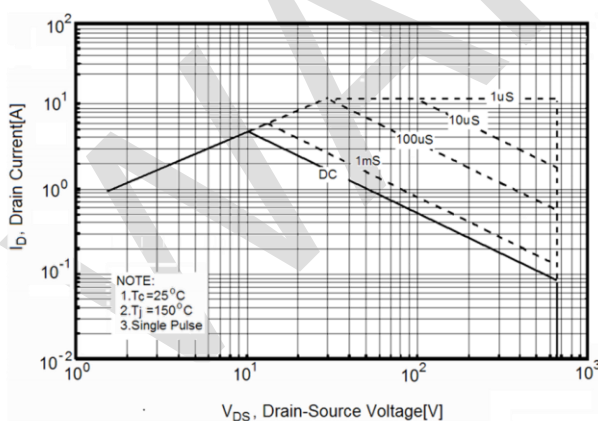
Maximum I_D vs Junction Temperature



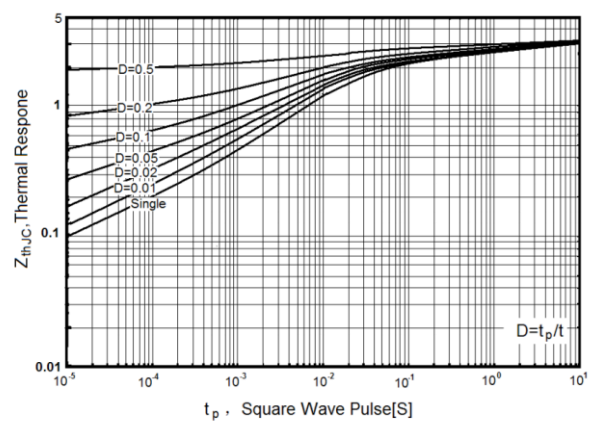
Gate charge waveforms



Capacitance

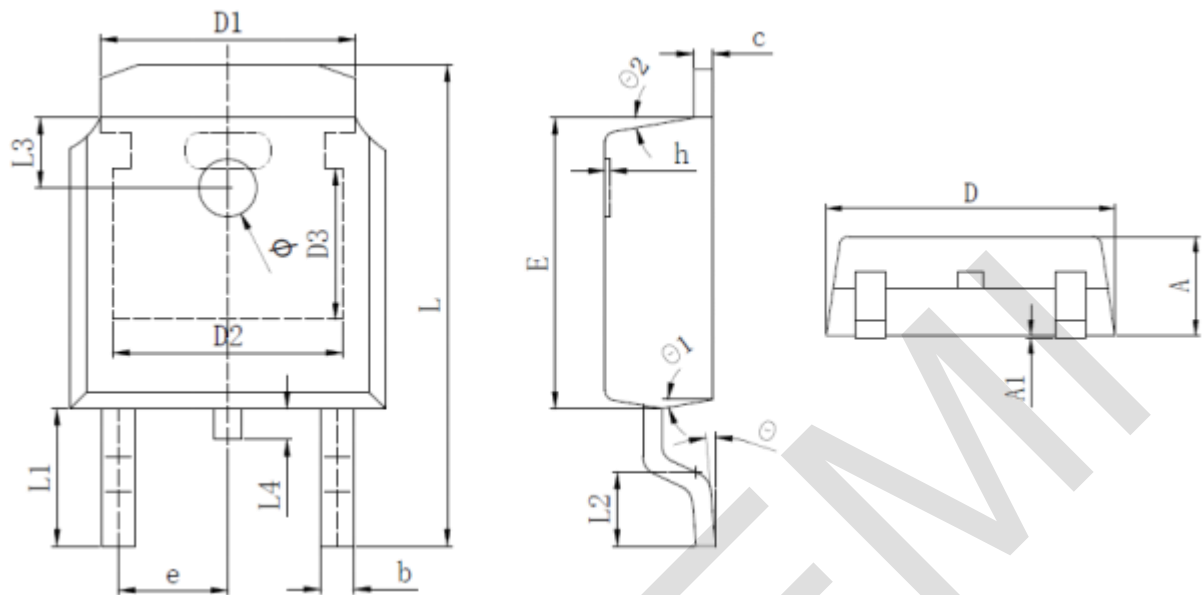


Safe operating area



Transient Thermal Impedance

8.Package Dimensions



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	2.200	2.300	2.400
A1	0.000		0.127
b	0.640	0.690	0.740
c(电镀后)	0.460	0.520	0.580
D	6.500	6.600	6.700
D1	5.334 REF		
D2	4.826 REF		
D3	3.166 REF		
E	6.000	6.100	6.200
e	2.286 TYP		
h	0.000	0.100	0.200
L	9.900	10.100	10.300
L1	2.888 REF		
L2	1.400	1.550	1.700
L3	1.600 REF		
L4	0.600	0.800	1.000
Φ	1.100	1.200	1.300
θ	0°		8°
θ1	9° TYP		
θ2	9° TYP		

9.Important Notice

WAN SEMICONDUCTOR (NINGBO) CO.,LTD reserves the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services and to discontinue any product or service. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as “components”) are sold subject to WANSEMI’s terms and conditions of sale supplied at the time of order acknowledgment.

WANSEMI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in WANSEMI’s terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent WANSEMI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

WANSEMI assumes no liability for applications assistance or the design of Buyers’ products. Buyers are responsible for their products and applications using WANSEMI components. To minimize the risks associated with Buyers’ products and applications, Buyers should provide adequate design and operating safeguards.

No WANSEMI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Unless WANSEMI has specifically designated certain components which meet ISO/TS16949 requirements, mainly for automotive use, WANSEMI will not be responsible for any failure of such components to meet such requirements.